

阅读申明

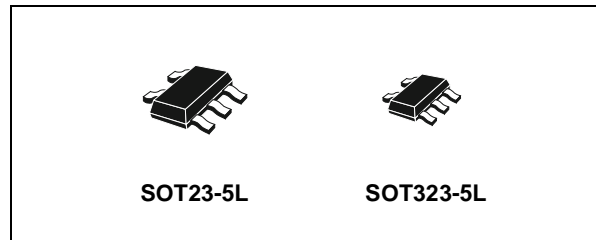
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SINGLE BUS BUFFER (3-STATE)

- HIGH SPEED: $t_{PD} = 3.4ns$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu A$ (MAX.) at $T_A=25^\circ C$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 8mA$ (MIN) at $V_{CC} = 4.5V$
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 2V$ to $5.5V$
- IMPROVED LATCH-UP IMMUNITY



ORDER CODES

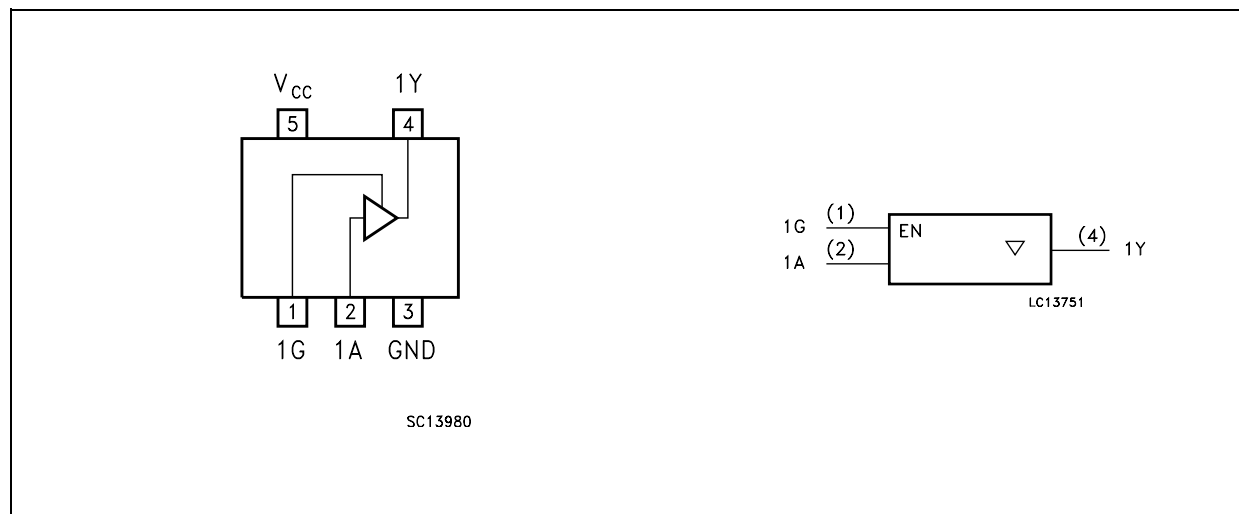
PACKAGE	T & R
SOT23-5L	74V1G126STR
SOT323-5L	74V1G126CTR

DESCRIPTION

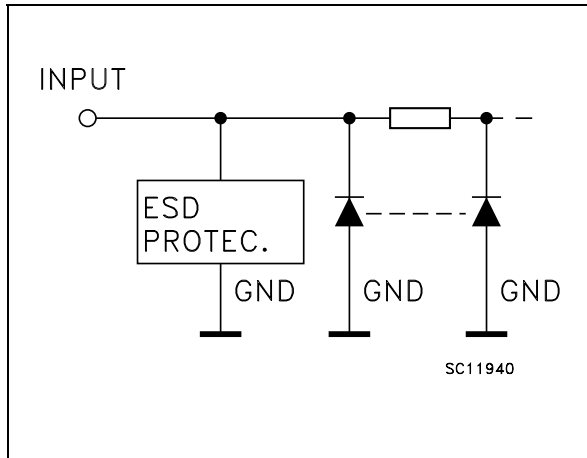
The 74V1G126 is an advanced high-speed CMOS SINGLE BUS BUFFER fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology.
3-STATE control input 1G has to be set LOW to place the output into the high impedance state.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1	1G	Output Enable Input
2	1A	Data Input
4	1Y	Data Output
3	GND	Ground (0V)
5	V _{CC}	Positive Supply Voltage

TRUTH TABLE

A	G	Y
X	L	Z
L	H	L
H	H	H

X : Don't Care
Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) (V _{CC} = 3.3 ± 0.3V) (V _{CC} = 5.0 ± 0.5V)	0 to 100 0 to 20	ns/V ns/V

1) V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		3.0 to 5.5		0.7V _{CC}			0.7V _{CC}		0.7V _{CC}		
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		3.0 to 5.5				0.3V _{CC}		0.3V _{CC}		0.3V _{CC}	
V _{OH}	High Level Output Voltage	2.0	I _O =-50 μA	1.9	2.0		1.9		1.9		V
		3.0	I _O =-50 μA	2.9	3.0		2.9		2.9		
		4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		
		3.0	I _O =-4 mA	2.58			2.48		2.4		
		4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output Voltage	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =50 μA		0.0	0.1		0.1		0.1	
		3.0	I _O =4 mA			0.36		0.44		0.55	
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _{OZ}	High Impedance Output Leakage Current	5.5	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.25		± 2.5		± 5	μA
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			1		10		20	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)	C _L (pF)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{PLH} t _{PHL}	Propagation Delay Time	3.3 ^(*)	15		4.7	7.5	1.0	8.5	1.0	9.5	ns
		3.3 ^(*)	50		5.2	8.0	1.0	9.5	1.0	10.5	
		5.0 ^(**)	15		3.4	5.5	1.0	6.5	1.0	7.5	
		5.0 ^(**)	50		3.7	6.5	1.0	7.5	1.0	8.5	
t _{PLZ} t _{PHZ}	Output Disable Time	3.3 ^(*)	15		4.4	8.0	1.0	9.0	1.0	10.0	ns
		3.3 ^(*)	50		4.8	11.5	1.0	12.5	1.0	13.5	
		5.0 ^(**)	15		3.0	5.0	1.0	6.0	1.0	7.0	
		5.0 ^(**)	50		3.2	7.0	1.0	8.0	1.0	9.0	
t _{PZL} t _{PZH}	Output Enable Time	3.3 ^(*)	15		4.8	7.6	1.0	9.5	1.0	10.5	ns
		3.3 ^(*)	50		5.3	8.5	1.0	10.0	1.0	11.0	
		5.0 ^(**)	15		3.6	5.9	1.0	7.0	1.0	8.0	
		5.0 ^(**)	50		3.9	6.5	1.0	7.5	1.0	8.5	

(*) Voltage range is 3.3V ± 0.3V

(**) Voltage range is 5.0V ± 0.5V

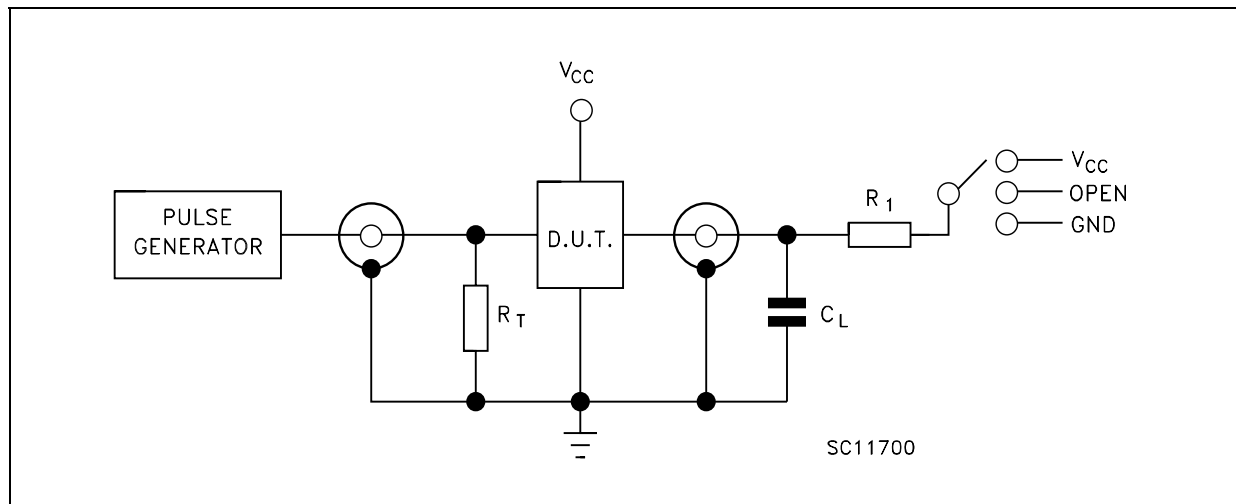


CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition	Value						Unit	
			T _A = 25°C			-40 to 85°C		-55 to 125°C		
			Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance			4	10			10		pF
C _{OUT}	Output Capacitance			10						pF
C _{PD}	Power Dissipation Capacitance (note 1)			10						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

TEST CIRCUIT

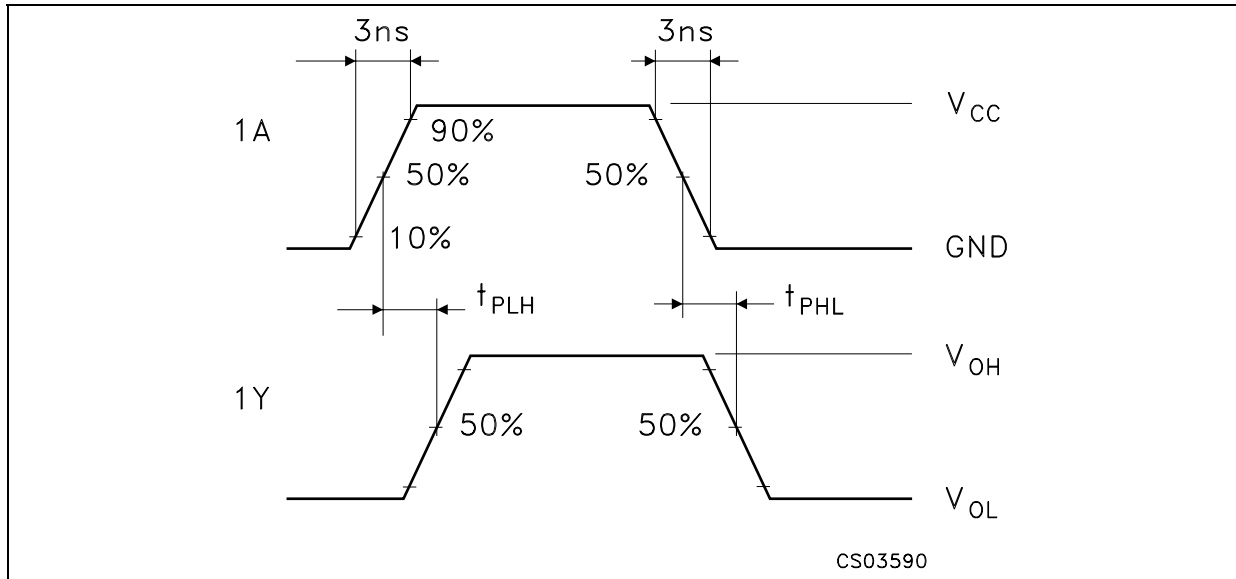
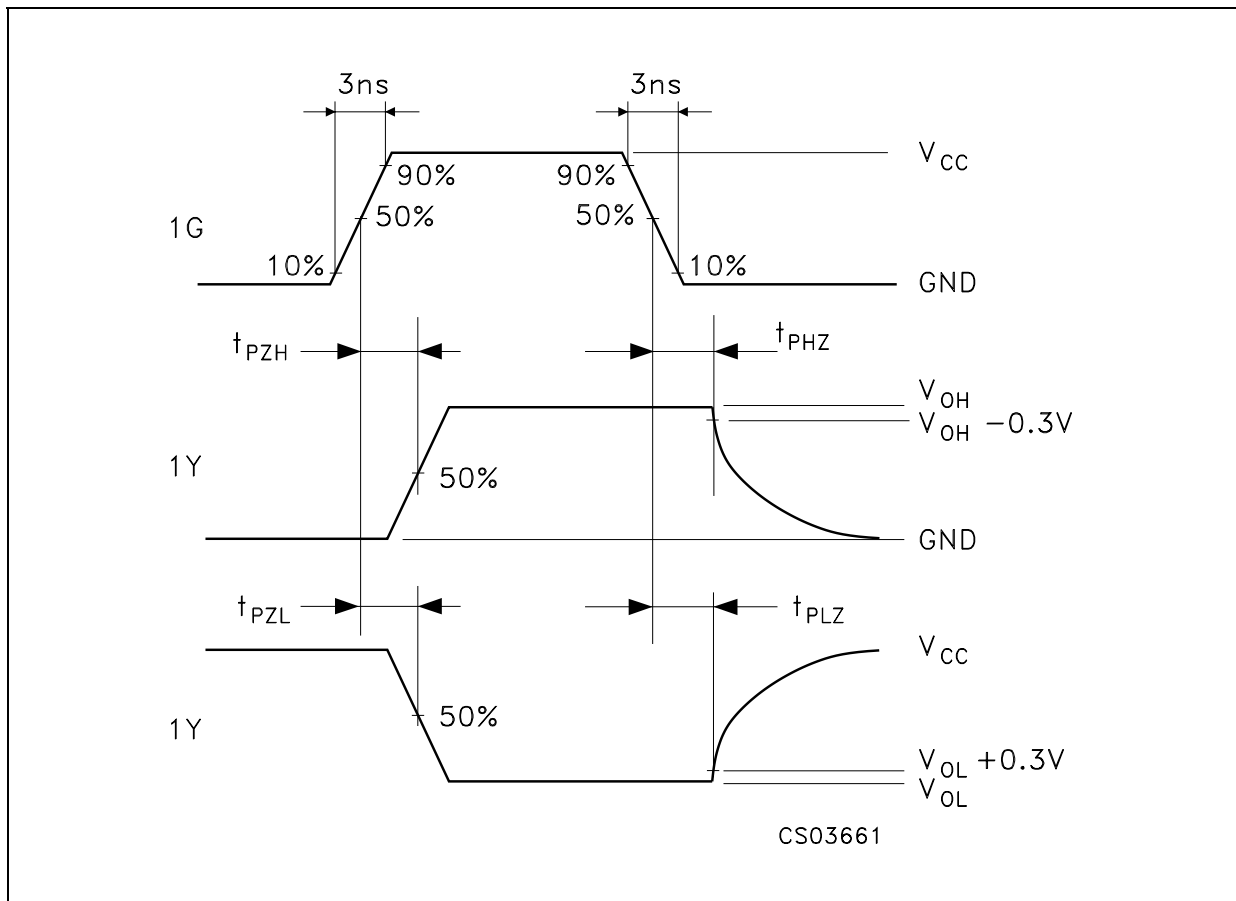


TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	V _{CC}
t _{PZH} , t _{PHZ}	GND

C_L = 15/50pF or equivalent (includes jig and probe capacitance)

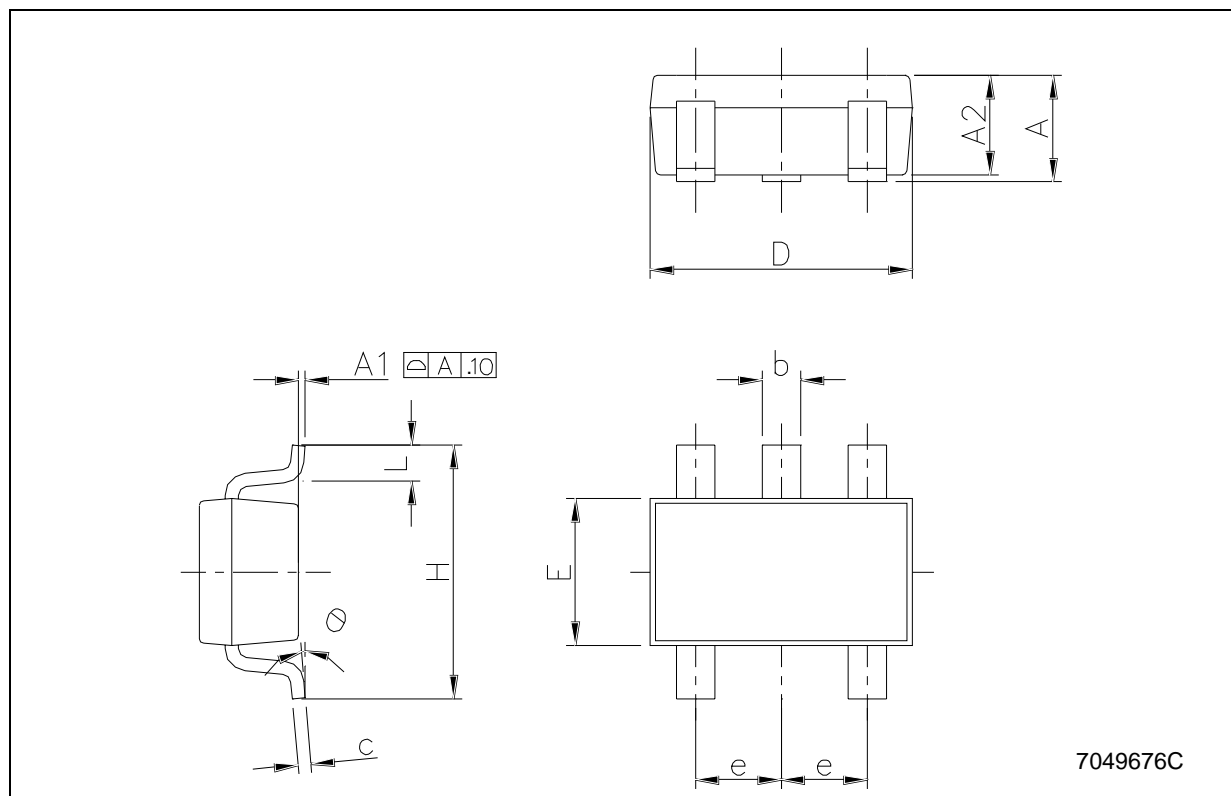
R₁ = 1KΩ or equivalent

R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)**WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME** ($f=1\text{MHz}$; 50% duty cycle)

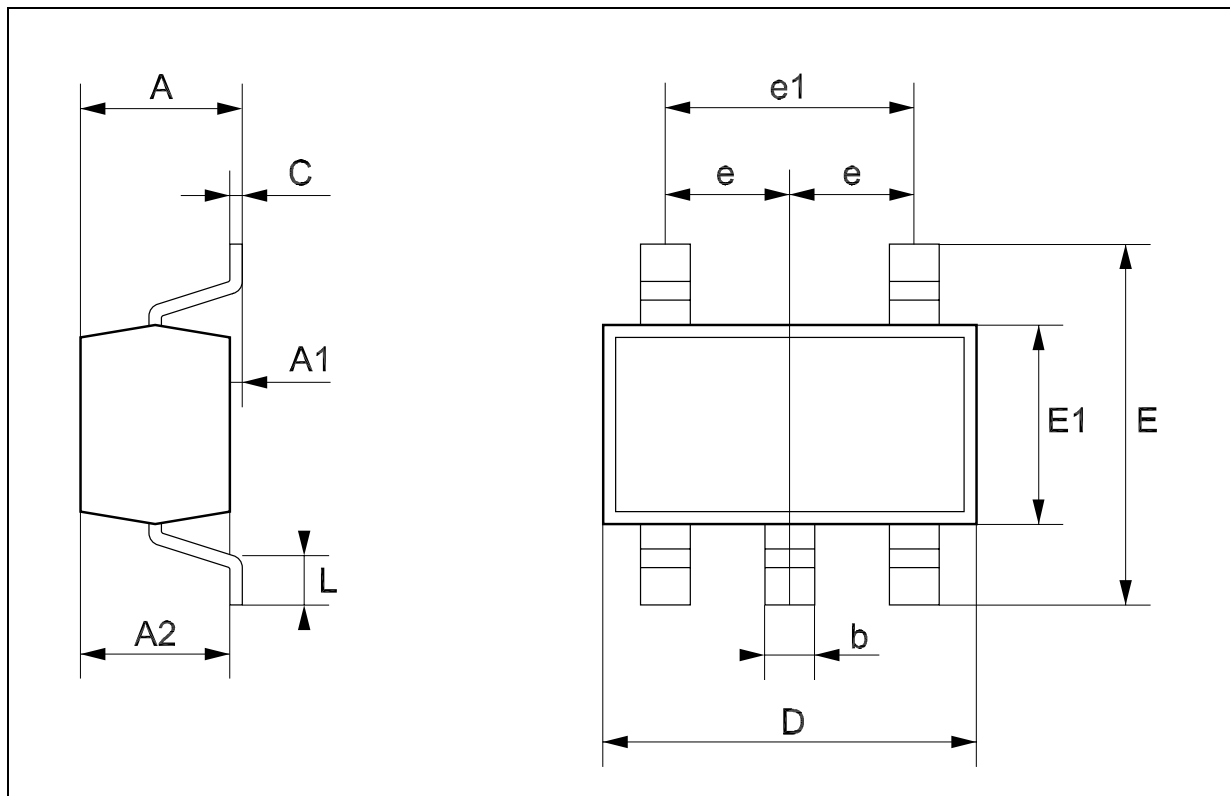
SOT23-5L MECHANICAL DATA

DIM.	mm.			mils		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.10	0.0		3.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	1.50		1.75	59.0		68.8
e		0.95			37.4	
H	2.60		3.00	102.3		118.1
L	0.10		0.60	3.9		23.6



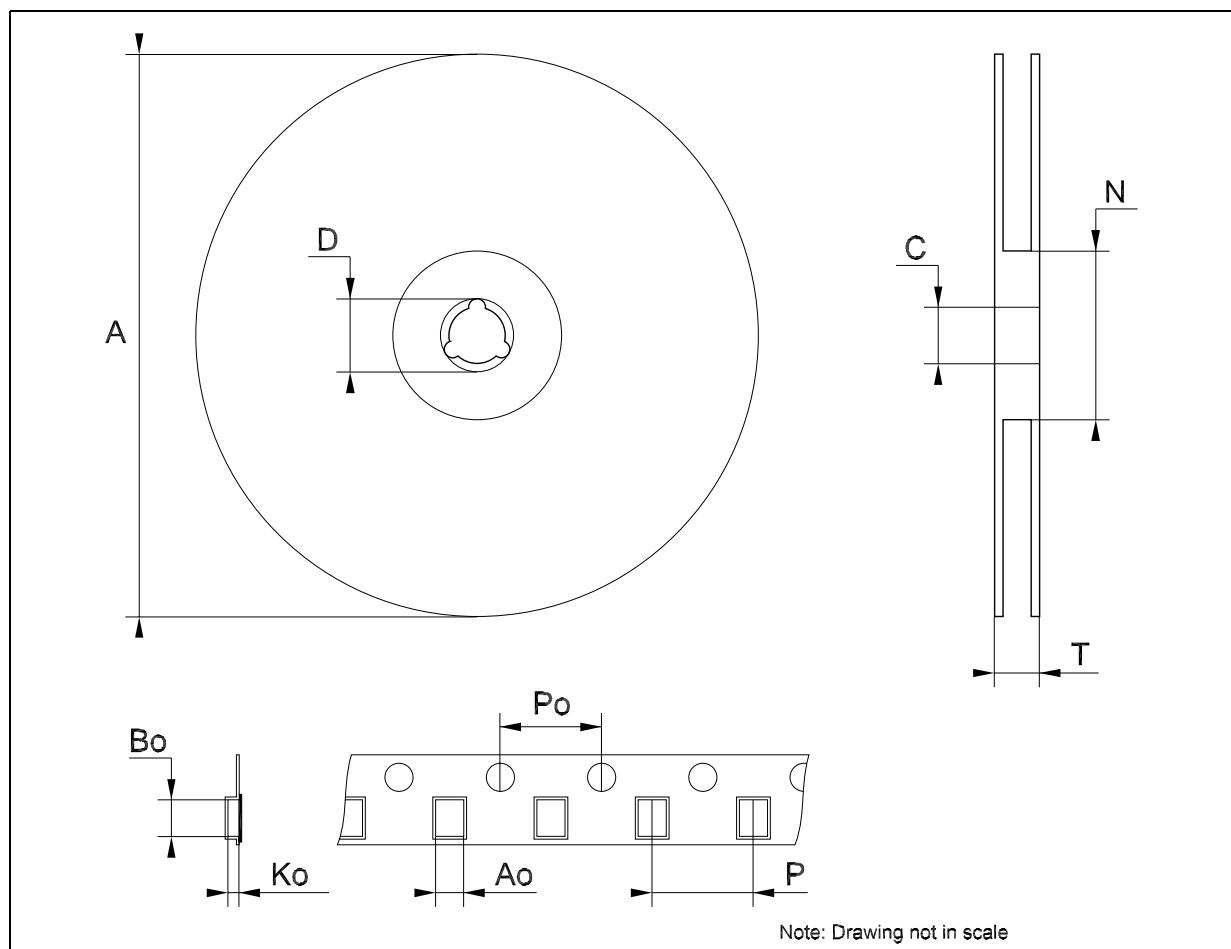
SOT323-5L MECHANICAL DATA

DIM.	mm.			mils		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	0.80		1.10	31.5		43.3
A1	0.00		0.10	0.0		3.9
A2	0.80		1.00	31.5		39.4
b	0.15		0.30	5.9		11.8
C	0.10		0.18	3.9		7.1
D	1.80		2.20	70.9		86.6
E	1.80		2.40	70.9		94.5
E1	1.15		1.35	45.3		53.1
e		0.65			25.6	
e1		1.3			51.2	
L	0.10		0.30	3.9		11.8



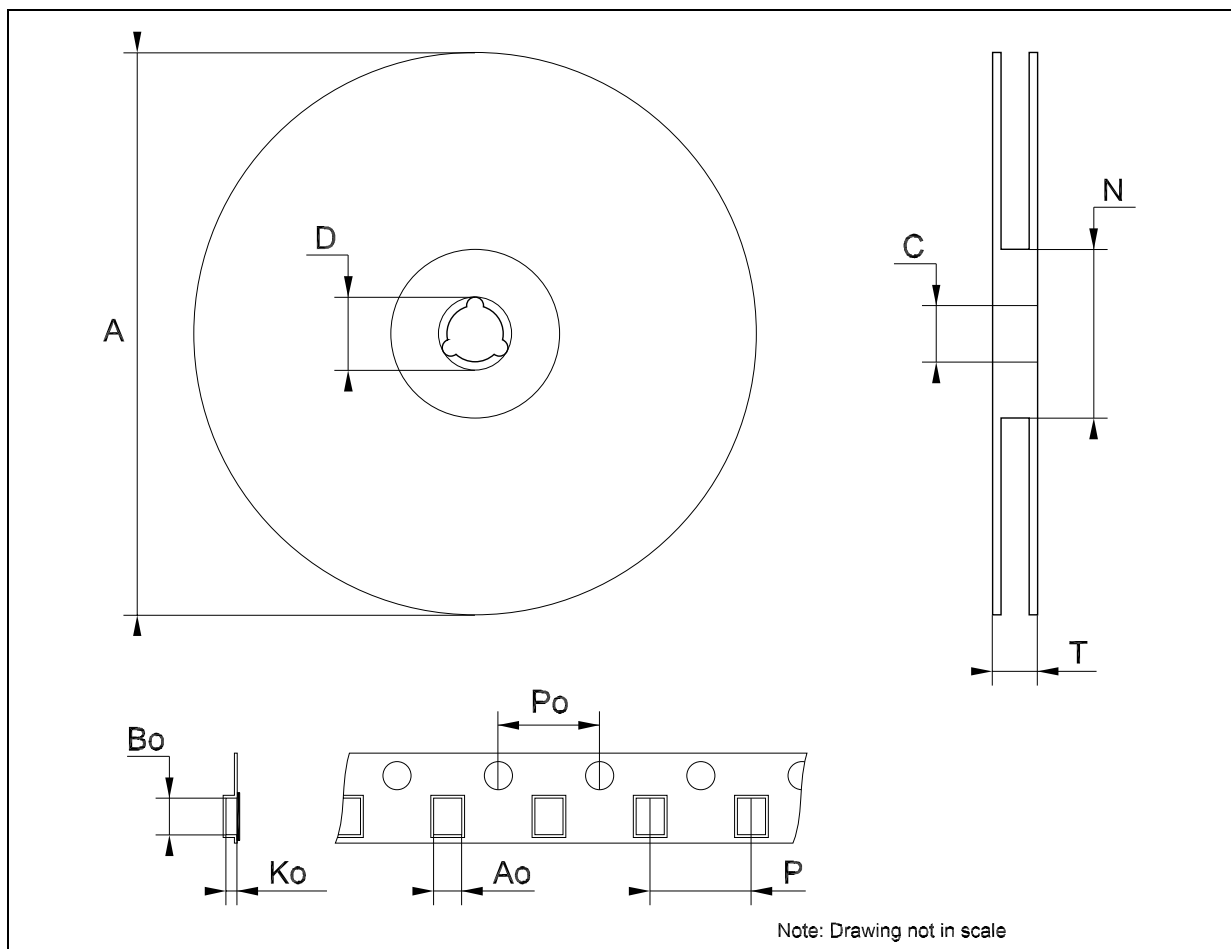
Tape & Reel SOT23-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			180			7.086
C	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	60			2.362		
T			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Bo	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.058
Po	3.9	4.0	4.1	0.153	0.157	0.161
P	3.9	4.0	4.1	0.153	0.157	0.161



Tape & Reel SOT323-xL MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	175	180	185	6.889	7.086	7.283
C	12.8	13	13.2	0.504	0.512	0.519
D	20.2			0.795		
N	59.5	60	60.5		2.362	
T			14.4			0.567
Ao		2.25			0.088	
Bo		2.7			0.106	
Ko		1.2			0.047	
Po	3.9	4	4.1	0.153	0.157	0.161
P	3.8	4	4.2	0.149	0.157	0.165



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